

Design Benefits

- Very low switching losses
- Fast reverse recovery
- Fast switching speed
- > Temperature independent turn-off switching losses
- > Very fast and robust intrinsic body diode
- Faster commutation and improved switching due to the additional Kelvin source pin

Key applications

- > E-vehicle charging infrastructure
- > Photovoltaic inverters
- > Switch mode power supply
- Uninterruptable power supply
- Motor drives

Key technical features

- > Best-in-class R_{DSon} temperature stability
- > Superior gate charge and beneficial gate charge ratio
 - Low power consumption of gate drivers
 - High tolerance against parasitic turn-on
- > Ultra small threshold voltage tolerance
- > Robust body diode with very low forward voltage
- > Lower leakage current up to 1200 V



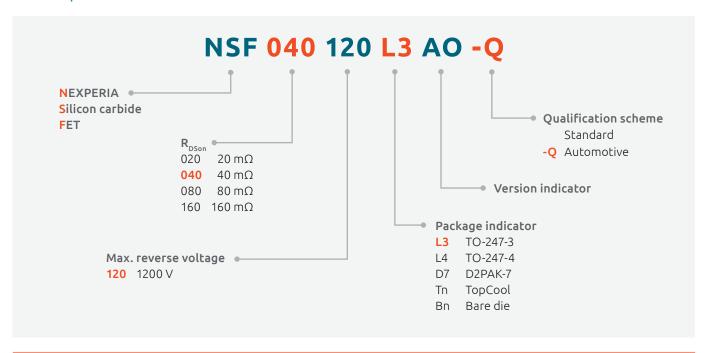
- > Datasheets
- Application notes
-) New
- > Videos and more



Product range

Type name	Package	V _{DS} max (V)	R_{DSon} typ (m Ω) @ $T_j = 25$ °C	I _D max (A) @ TC = 25 °C	T _j max (°C)
NSF030120L3A0			30	67	
NSF040120L3A0	25		40	65	
NSF060120L3A0			60	38	
NSF080120L3A0	TO-247-3		80	35	
NSF030120L4A0			30	67	
NSF040120L4A0	26		40	65	
NSF060120L4A0		1200	60	38	175
NSF080120L4A0	TO-247-4		80	35	
NSF030120D7A0			30	67	
NSF040120D7A0	DIPA-T		40	65	
NSF060120D7A0	199999		60	38	
NSF080120D7A0	TO-263-7		80	33	

SiC FET | Nomenclature



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Date of release:

July 2024

Printed:

In the Netherlands

